

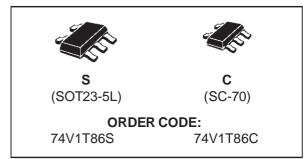
74V1T86

SINGLE EXCLUSIVE OR GATE

- HIGH SPEED: tpD = 5 ns (TYP.) at Vcc = 5V
- LOW POWER DISSIPATION: $I_{CC} = 1 \mu A \text{ (MAX.)}$ at $T_A = 25 \, ^{\circ}\text{C}$
- COMPATIBLE WITH TTL OUTPUTS: V_{IH} = 2V (MIN), V_{IL} = 0.8V (MAX)
- POWER DOWN PROTECTION ON INPUTS & OUTPUT
- SYMMETRICAL OUTPUT IMPEDANCE: |IOH| = IOL = 8 mA (MIN)
- BALANCED PROPAGATION DELAYS: tplh ≅ tphl
- OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 4.5V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

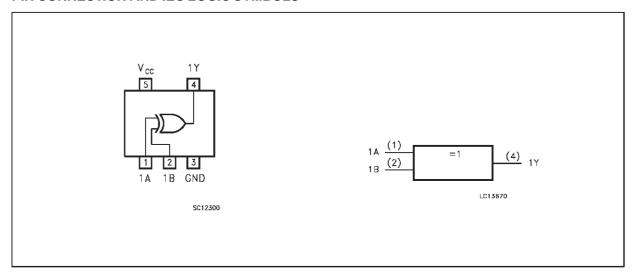
The 74V1T86 is an advanced high-speed CMOS SINGLE EXCLUSIVE OR GATE fabricated with sub-micron silicon gate and double-layer metal



wiring C²MOS technology.

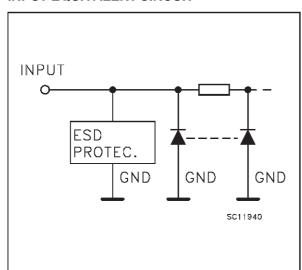
Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

PIN CONNECTION AND IEC LOGIC SYMBOLS



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INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	1A	Data Input
2	1B	Data Input
4	1Y	Data Output
3	GND	Ground (0V)
5	V _{CC}	Positive Supply Voltage

TRUTH TABLE

Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 1)	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 2)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
lok	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
Icc or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	4.5 to 5.5	V
V_{I}	Input Voltage	0 to 5.5	V
Vo	Output Voltage (see note 1)	0 to 5.5	V
Vo	Output Voltage (see note 2)	0 to Vcc	V
T _{op}	Operating Temperature	-40 to +85	°C
dt/dv	Input Rise and Fall Time (see note 3) $(V_{CC} = 5.0 \pm 0.5V)$	0 to 20	ns/V

¹⁾ Vcc = 0V

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¹⁾ $V_{CC} = 0V$

²⁾ High or Low State

²⁾ High or Low State

³⁾V_{IN} from 0.8V to 2 V

DC SPECIFICATIONS

Symbol	Parameter	Tes	t Conditions			Value			Unit
		Vcc		T _A = 25 °C			-40 to 85 °C		
		(V)		Min.	Тур.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	4.5 to 5.5		2			2		٧
VIL	Low Level Input Voltage	4.5 to 5.5				0.8		0.8	V
V _{OH}	High Level Output	4.5	I _O =-50 μA	4.4	4.5		4.4		V
	Voltage	4.5	I _O =-8 mA	3.94			3.8		v
V _{OL}	Low Level Output	4.5	I _O =50 μA		0.0	0.1		0.1	V
	Voltage	4.5	I _O =8 mA			0.36		0.44	V
I _I	Input Leakage Current	0 to 5.5	$V_I = 5.5V$ or GND			±0.1		±1.0	μΑ
Icc	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10	μΑ
Δl _{CC}	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V_{CC} or GND			1.35		1.5	mA
I _{OPD}	Output Leakage Current	0	V _{OUT} = 5.5V	0		0.5		5.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3 \text{ ns}$)

Symbol	Parameter	Test Condition				Value				Unit
		V _{CC} (*)	C∟		T _A = 25 °C		-40 to	85 °C		
		(V)	(pF)		Min.	Тур.	Max.	Min.	Max.	
t _{PLH}	Propagation Delay	5.0	15			5.0	7.9	1.0	9.0	nc
t _{PHL}	Time	5.0	50			5.5	7.9	1.0	9.0	ns

^(*) Voltage range is 5V ± 0.5V

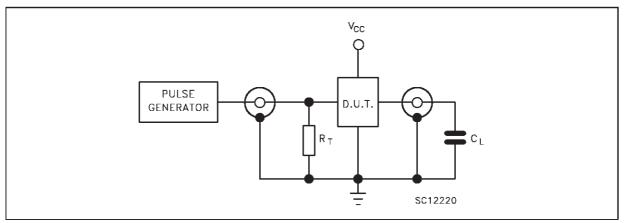
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions	Value					Unit
			T _A = 25 °C			-40 to 85 °C		
			Min.	Тур.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			4	10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			18				pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$

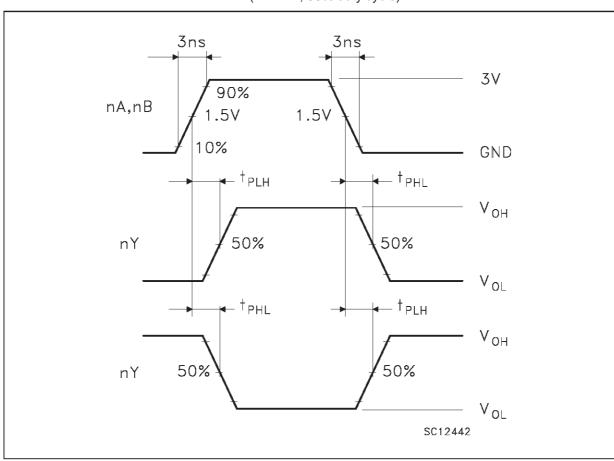


TEST CIRCUIT



 C_L = 15/50 pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically $50\Omega)$

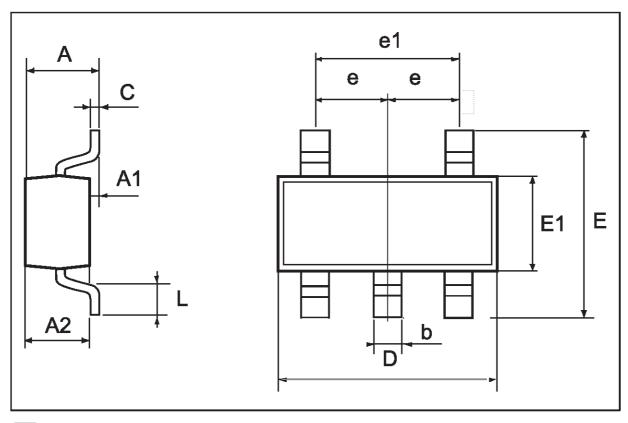
WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



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SOT23-5L MECHANICAL DATA

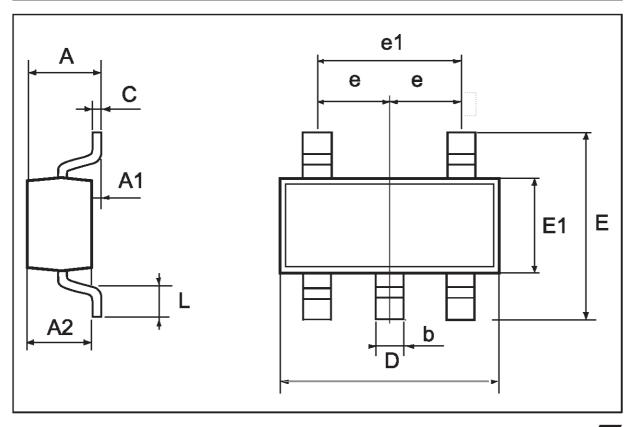
DIM.		mm		mils		
J	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
С	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
L	0.35		0.55	13.7		21.6
е		0.95			37.4	
e1		1.9			74.8	



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SC-70 MECHANICAL DATA

DIM.		mm		mils			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	0.80		1.10	31.5		43.3	
A1	0.00		0.10	0.0		3.9	
A2	0.80		1.00	31.5		39.4	
b	0.15		0.30	5.9		11.8	
С	0.10		0.18	3.9		7.1	
D	1.80		2.20	70.9		86.6	
E	1.80		2.40	70.9		94.5	
E1	1.15		1.35	45.3		53.1	
L	0.10		0.30	3.9		11.8	
е		0.65			25.6		
e1		1.3			51.2		



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